

Docket No.: 57810-093

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
Hideaki FUJIWARA, et al.	:	Confirmation Number:
	:	
Serial No.:	:	Group Art Unit:
	:	
Filed: March 23, 2004	:	Examiner: Unknown
	:	
For: SEMICONDUCTOR DEVICE INCLUDING FIELD-EFFECT TRANSISTOR		

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop IDS  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

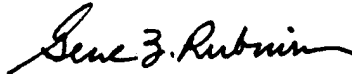
The relevance of the article, "Transistor Elements for 30nm Physical Gate Length and Beyond" is discussed in the present specification.

**Serial No.:**

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

A handwritten signature in black ink, appearing to read "Gene Z. Robinson".

Gene Z. Robinson

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**Date: March 23, 2004**

INFORMATION DISCLOSURE CITATION IN AN APPLICATION						ATTY. DOCKET NO. <b>57810-093</b>		SERIAL NO.	
(PTO-1449)						APPLICANT <b>Hideaki FUJIWARA, et al.</b>			
						FILING DATE <b>March 23, 2004</b>		GROUP	
U.S. PATENT DOCUMENTS									
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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FOREIGN PATENT DOCUMENTS									
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation			
						Yes	No		
		JP P2002-94058A	03/29/2002	TOSHIBA CORP		(Japan w/English Abstract)			
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)									
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.							
		Brian DOYLE, et al. "Transistor Elements for 30nm Physical Gate Lengths and Beyond", Intel Technology Journal, Vol. 6, Issue 2, May 16, 2002, ISSN 1535766X							
EXAMINER				DATE CONSIDERED					

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.